ever, today's atomic physics itself points to the limits of the "post-Newtonian" method—therefore it can provide useful analogies for other fields.

The book contains many striking aphorisms. Let me quote two examples. From "Changing Thought Pattern in Science" (chapter 12), "I now come back, in conclusion, to the question I posed at the beginning: 'How does one make a revolution?' And I shall assume for a moment, experimentally as it were, and without arguing with the historians, that the answer may be valid in all fields at once. It would then run: 'by trying to change as little as possible.' " And from chapter 15, "Science in the Contemporary University," we read "The dispute about specific percentages in joint decision-making strikes me as resembling the struggle of children over a toy that they have long since broken in the quarrel, and in which it can no longer matter how large a piece each of them retains."

The translation reads easily and has obviously been done with great care, but all the same I had occasionally some difficulty to understand what was meant until I translated back into German.

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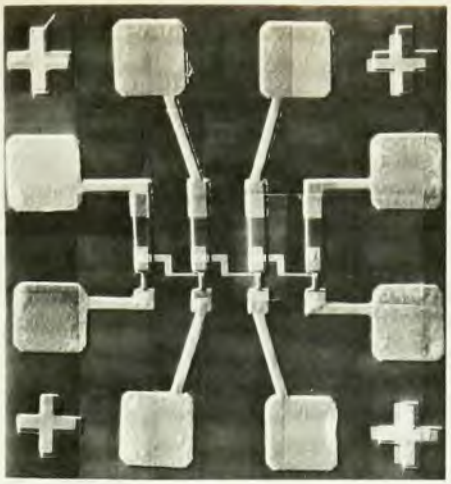
Gunn-effect Logic Devices

H. L. Hartnagel
138 pp. Elsevier, New York, 1973.
$21.00

The search for ever-faster logic processing elements has led to the application of new technologies to old devices and the application of relatively "old" devices in the logic field. This monograph by Hans Hartnagel of the University of Newcastle-upon-Tyne treats an example of the latter: the use of the traveling domains of high electric field that can exist in those semiconductors, such as GaAs, that can exhibit a bulk negative differential conductivity, to perform digital functions at high speed. Some excellent work has been done in this new field, and this volume comes at an appropriate time to serve as a useful introduction to the growing coalescence of digital and microwave semiconductor techniques.

Hartnagel is responsible for some of the earliest publications concerning the theory of two-terminal Gunn-effect logic devices and has since been involved with applications of these logic elements in communications systems. He treats in detail the major physical phenomena involved in Gunn-effect



The electron micrograph shows four Schottky-gate-triggered Gunn devices connected for pulse regeneration. Work done by K. Mause, et al. at the German Post Office.

logic elements and briefly surveys both experimentally verified and conjectural applications of these elements. Thus, the basic principles of Gunn-effect domain formation and travel are reviewed at some length, and then the implications of the planar structure of Gunn-effect logic elements on these domain dynamics are considered. The author describes the configuration, fabrication technology (very briefly) and performance of some simple logic elements and systems, such as adders and shift registers. He devotes a chapter largely to his own work on Gunn-effect digital communication systems and concludes with a chapter on some unusual and as-yet-unrealized logic applications that utilize domain formation and transit phenomena.

Unfortunately, Hartnagel does not seem fully convinced about the usefulness of three-terminal (Schottky-gate) devices, as compared to the two terminal devices. In fact, most of the work that has been done on Gunn-effect logic devices that can be seen to have some bearing on practical applications has been done on Schottky-gate devices. Thus it would have been helpful if he had included more technical and less purely descriptive material on these devices.

The author has ignored some important aspects of the systems integration of these logic devices. For example, there is no discussion of device fanout, noise margin, logic swing or interfacing with other types of logic devices. In addition, in a comparison between Gunn-effect devices and GaAs Schottky-gate FET's, the discussion of carrier velocities is unclear and does not take into account the results of Ruch and others on transient phenomena occurring in FET's.

Finally, it would have been expected that such an expensive book would have had a more complete bibliography with many more in-text references and a far more complete index. Many of the illustrations of experimental configurations and results, while understandable in themselves, refer to unreferenced work, so that a reader desiring to obtain more complete information would not be able to easily do so.

Hartnagel's book, while slightly flawed, nevertheless should serve as a useful introduction to the more general aspects of the field of Gunn-effect logic devices, with an emphasis on the major physical phenomena occurring in these devices.

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Communication with Extraterrestrial Intelligence

Carl Sagan, ed.
428 pp. MIT Press, Cambridge, Mass., 1973. $10.00

Possibly the most important interdisciplinary scientific problem under discussion today is the possible existence of extraterrestrial civilizations, and the chance that we may enter into communication with one or more of them. This book contains the proceedings of a conference held 5–11 September 1971, at the Byurakan Astrophysical Observatory of the Armenian Academy of Sciences, USSR. The conference was jointly arranged by the Academies of Science of the US and the USSR, so it is not too surprising that most of the participants came from these two countries: 32 from the USSR, 18 from the US, and only 4 from other countries. The book contains the edited transcripts of the presentations plus the accompanying discussion (which was extensive) together with a number of brief scientific notes presented as appendices.

Most attempts to quantify the probable number of intelligent civilizations in the galaxy capable of communicating with us, N, have centered around the following probability expression:

$$N = R_* f_p n_e f_l f_i f_c L$$

Here R_* is the number of stars formed per year averaged over the lifetime of the galaxy, f_p is the fraction of stars that have planetary systems, n_e is the number of planets within such planetary systems that have conditions suitable for life, f_l is the fraction of such planets on which life actually begins, f_i is the fraction of such planets on which life develops some form of intelligence, f_c is the fraction of these in which the intelligent beings develop